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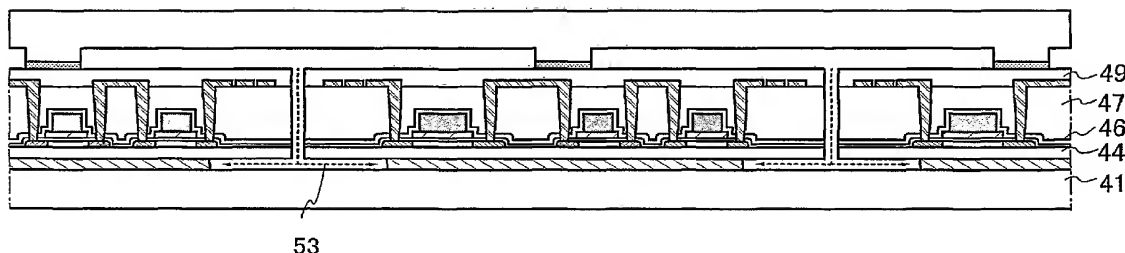
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(54) Title: METHOD FOR MANUFACTURING THIN FILM INTEGRATED CIRCUIT DEVICE, NONCONTACT THIN FILM INTEGRATED CIRCUIT DEVICE AND METHOD FOR MANUFACTURING THE SAME, AND IDTAG AND COIN INCLUDING THE NONCONTACT THIN FILM INTEGRATED CIRCUIT DEVICE



(57) Abstract: To provide a thin film integrated circuit which is mass produced at low cost, a method for manufacturing a thin film integrated circuit according to the invention includes the steps of: forming a peel-off layer over a substrate; forming a base film over the peel-off layer; forming a plurality of thin film integrated circuits over the base film; forming a groove at the boundary between the plurality of thin film integrated circuits; and introducing a gas or a liquid containing halogen fluoride into the groove, thereby removing the peel-off layer; thus, the plurality of thin film integrated circuits are separated from each other.



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